

Abstracts

GaAs MESFET Optimization and New Device Applications Based on Wave Property Studies

K. Fricke and H.L. Hartnagel. "GaAs MESFET Optimization and New Device Applications Based on Wave Property Studies." 1985 MTT-S International Microwave Symposium Digest 85.1 (1985 [MWSYM]): 192-195.

The results to be presented are obtained by an experimental investigation of the wave properties on FET structures using especially fabricated MESFETs. The use of this information for an optimization of MESFET structures and for a development of new devices is discussed. It will be demonstrated that a significant improvement of the FET gain is obtainable.

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